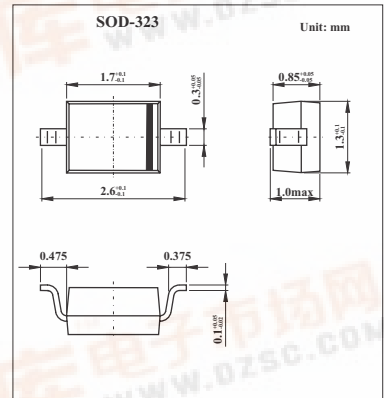


SMD Type Diodes

Silicon Epitaxial Planar Diode  
1SV324

Features

- High Capacitance Ratio:C1V/C4V=4.3(Typ.)
- Low Series Resistance:rs=0.4 Ω (Typ.)
- Useful for Small Size Tuner



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	10	V
Junction Temperature	T <sub>j</sub>	125	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +125	°C

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	V <sub>R</sub>	I <sub>R</sub> = 1 μ A	10			V
Reverse Current	I <sub>R</sub>	V <sub>R</sub> = 10 V			3	nA
Capacitance	C <sub>1V</sub>	f = 1 MHz; V <sub>R</sub> = 1 V	44		49.5	pF
	C <sub>4V</sub>	f = 1 MHz; V <sub>R</sub> = 4 V	9.2		12	
Capacitance Ratio	C <sub>1V</sub> /C <sub>4V</sub>		4	4.3		
Series Resistance	r <sub>s</sub>	V <sub>R</sub> = 4V, f = 470 MHz		0.4	0.8	Ω

Note

1.Signal level when capacitance is measured:Vsig = 500mVrms

Marking

Marking	V8
---------	----